

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes Examiner: Unknown
Serial No.: Unknown Group Art Unit: Unknown
Filed: Herewith Docket: 1303.058US2
Title: FERROELECTRIC WRITE ONCE READ ONLY MEMORY FOR ARCHIVAL
STORAGE

INFORMATION DISCLOSURE STATEMENT

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicant's prior U.S. application, Serial No. 10/177082, filed on June 21, 2002, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES

By his Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6944

Date 2-27-04

By 
David C. Peterson
Reg. No. 47,857

"Express Mail" mailing label number: EV299684051 US

Date of Deposit: February 27, 2004

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Mail Stop Patent Application, P.O.Box 1450, Alexandria, VA 22313-1450.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 1 of 8		Attorney Docket No: 1303.058US2	

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US020109158	08/15/2002	Forbes, Leonard , et al.	257	224	02/09/2001
	US20020027264A1	03/07/2002	Forbes, Leonard , et al.	257	662	08/08/2001
	US20020155688	10/24/2002	Ahn, Kie Y., et al.	438	592	04/20/2001
	US20020155689	10/24/2002	Ahn, Kie Y., et al.	29	76	02/11/2002
	US20020192974	12/19/2002	Ahn, Kie Y., et al.	438	722	06/13/2001
	US20020036939A1	03/28/2002	Tsai, Wen-Jer , et al.	365	201	08/30/2001
	US20020074565A1	06/20/2002	Flagan, R. C., et al.	257	200	06/29/2001
	US20030017717	01/23/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-3,641,516	02/01/1972	Casrucci, Paul P., et al.	365	96	
	US-3,665,423	05/23/1972	Nakamura, Sho , et al.			
	US-3,877,054	04/08/1975	Boulin, David M., et al.	357	23	
	US-3,964,085	06/15/1976	Kahng, Duwon , et al.	428	428	08/18/1975
	US-4,152,627	05/01/1979	Priel, Ury , et al.	315	227	06/10/1977
	US-4,217,601	08/12/1980	DeKeersmaecker, Roger F., et al.	357	54	
	US-4,888,733	12/19/1989	Mobley, Kenneth J.	365	145	09/12/1988
	US-5,042,011	08/20/1991	Casper, Stephen L., et al.	365	205	05/22/1989
	US-5,280,205	06/18/1994	Green, Robert S., et al.	307	530	04/16/1992
	US-5,399,516	03/21/1995	Bergendahl, A. , et al.	437	43	09/21/1992
	US-5,410,504	04/25/1995	Ward, Calvin B.	365	149	05/03/1994
	US-5,457,649	10/10/1995	Eichman, Eric C., et al.	365	174	08/26/1994
	US-5,530,581	06/25/1996	Cogan, S. F.	359	265	05/31/1995
	US-5,530,668	06/25/1996	Chern, Wen-Foo , et al.	365	145	04/12/1995
	US-5,539,279	07/23/1996	Takeuchi, Kan , et al.	365	145	12/22/1994
	US-5,541,871	07/30/1996	Nishimura, K. , et al.	365	145	01/18/1995
	US-5,550,770	08/27/1996	Kuroda, Kenichi	365	145	06/02/1995
	US-5,572,459	11/05/1996	Wilson, Dennis R., et al.	365	145	09/16/1994
	US-5,600,587	02/04/1997	Koike, Hiorki	365	145	01/29/1996
	US-5,627,785	05/06/1997	Gilliam, Gary R., et al.	365	189.01	03/15/1996

EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known				
		Application Number		Unknown		
		Filing Date		Even Date Herewith		
		First Named Inventor		Forbes, Leonard		
		Group Art Unit		Unknown		
		Examiner Name		Unknown		
Sheet 2 of 8		Attorney Docket No: 1303.058US2				

	US-5,740,104	04/14/1998	Forbes, Leonard	365	185.03	01/29/1997
	US-5,768,192	06/16/1998	Eitan, Boaz	365	185.24	07/23/1996
	US-5,801,401	09/01/1998	Forbes, Leonard	257	77	01/29/1997
	US-5,828,605	10/27/1998	Peng, K. , et al.	365	185.29	10/14/1997
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5,856,688	01/05/1999	Lee, K. , et al.	257	295	09/30/1997
	US-5,886,368	03/23/1999	Forbes, Leonard , et al.	257	77	07/29/1997
	US-5,912,488	06/15/1999	Kim, D. M., et al.	257	316	06/24/1997
	US-5,936,274	08/10/1999	Forbes, Leonard , et al.	257	315	07/08/1997
	US-5,943,262	08/24/1999	Choi, J.	365	185.17	10/28/1998
	US-5,973,356	10/26/1999	Noble, Wendell P., et al.	257	319	07/08/1997
	US-5,989,958	11/23/1999	Forbes, Leonard	438	257	08/20/1998
	US-5,991,225	11/23/1999	Forbes, Leonard , et al.	365	230.06	02/27/1998
	US-6,031,263	02/29/2000	Forbes, Leonard , et al.	257	315	07/29/1997
	US-6,034,882	03/07/2000	Johnson, Mark G., et al.	365	103	11/16/1998
	US-6,072,209	06/06/2000	Noble, Wendell P., et al.	257	296	07/08/1997
	US-6,115,281	09/05/2000	Aggarwal, S., et al.	365	145	09/11/1998
	US-6,125,062	09/26/2000	Ahn, Kie , et al.	365	198.07	08/26/1998
	US-6,140,181	10/31/2000	Forbes, Leonard , et al.	438	257	09/10/1999
	US-6,141,237	10/31/2000	Eliason, Jarrod , et al.	365	145	07/12/1999
	US-6,141,238	10/31/2000	Forbes, L. , et al.	365	145	08/30/1999
	US-6,141,260	10/31/2000	Ahn, Kie , et al.	365	189.07	08/27/1998
	US-6,143,636	11/07/2000	Forbes, Leonard , et al.	438	587	08/20/1998
	US-6,150,687	11/21/2000	Noble, Wendell P., et al.	257	302	07/08/1997
	US-6,153,468	11/28/2000	Forbes, Leonard , et al.	438	257	05/17/1999
	US-6,166,401	12/26/2000	Forbes, L.	257	77	08/20/1998
	US-6,185,122	02/06/2001	Johnson, Mark G., et al.	365	103	12/22/1999
	US-6,203,613	03/20/2001	Gates, Stephen M., et al.	117	104	10/19/1999
	US-6,212,103	04/03/2001	Ahrens, Michael G., et al.	365	18529	07/28/1999

EXAMINER

DATE CONSIDERED

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 3 of 8		Attorney Docket No: 1303.058US2	

	US-6,232,643	05/15/2001	Forbes, Leonard , et al.	257	405	11/13/1997
	US-6,238,976	05/29/2001	Noble, Wendell P., et al.	438	259	02/27/1998
	US-6,243,300	06/05/2001	Sunkavalli, Ravi S.	365	185.29	02/16/2000
	US-6,246,606	06/12/2001	Forbes, Leonard , et al.	365	185.03	09/02/1999
	US-6,249,020	06/19/2001	Forbes, Leonard , et al.	257	315	08/27/1998
	US-6,252,793	06/26/2001	Allen, Judith E., et al.	365	145	09/15/2000
	US-6,269,023	07/31/2001	Derhacobian, Narbeh , et al.	365	185.24	10/23/2000
	US-6,281,144	08/28/2001	Cleary, Thomas J., et al.	438	780	07/15/1999
	US-6,294,813	09/25/2001	Forbes, Leonard , et al.	257	321	02/15/2000
	US-6,297,539	10/02/2001	Ma, Yanjun , et al.	257	410	07/06/2000
	US-6,302,964	10/16/2001	Umotoy, Salvador P., et al.	118	715	03/16/2000
	US-6,303,481	10/16/2001	Park, Dong	438	591	12/29/2000
	US-6,313,518	11/06/2001	Ahn, K. , et al.	257	632	03/02/2000
	US-6,337,805	01/08/2002	Forbes, Leonard , et al.	365	145	12/15/1999
	US-6,351,411	02/26/2002	Forbes, Leonard , et al.	365	182	06/12/2001
	US-6,368,941	04/09/2002	Chen, Tai-Ju , et al.	438	424	11/08/2000
	US-6,380,579	04/30/2002	Nam, Sang-don , et al.	257	306	04/11/2000
	US-6,387,712	05/14/2002	Yano, Yoshihiko , et al.	438	3	12/03/1999
	US-6,391,769	05/21/2002	Lee, Jong-myeong , et al.	438	643	03/14/2000
	US-6,407,435	06/18/2002	Ma, Yanjun , et al.	257	411	02/11/2000
	US-6,432,779	08/13/2002	Hobbs, Christopher , et al.	438	287	01/30/2001
	US-6,438,031	08/20/2002	Fastow, Richard M.	365	185.18	10/26/2000
	US-6,444,039	09/03/2002	Nguyen, Tue	118	715	03/07/2000
	US-6,444,895	09/03/2002	Nikawa, Kiyoshi	136	212	09/24/1999
	US-6,445,023	09/03/2002	Vaartstra, Brian , et al.	257	295	03/16/1999
	US-6,445,030	09/03/2002	Wu, Yider , et al.	257	315	01/30/2001
	US-6,449,188	09/10/2002	Fastow, R.	365	185.18	06/19/2001
	US-6,456,531	09/24/2002	Wang, Janet S., et al.	365	185.18	06/19/2001
	US-6,456,536	09/24/2002	Sobek, Daniel , et al.	365	185.28	06/19/2001

EXAMINER

DATE CONSIDERED

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 4 of 8		Attorney Docket No: 1303.058US2	

	US-6,458,701	10/01/2002	Chae, Yun-sook , et al.	438	680	10/12/2000
	US-6,459,618	10/01/2002	Wang, Janet S.	365	185.18	06/13/2001
	US-6,465,334	10/15/2002	Buynoski, Matthew S., et al.	438	591	10/05/2000
	US-6,487,121	11/26/2002	Thurgate, Timothy J., et al.	365	185.18	07/05/2001
	US-6,495,436	12/17/2002	Ahn, Kie Y., et al.	438	591	02/09/2001
	US-6,498,362	12/24/2002	Forbes, Leonard , et al.	257	295	08/26/1999
	US-6,514,828	02/04/2003	Ahn, Kie Y., et al.	438	297	04/20/2001
	US-6,521,911	02/18/2003	Parsons, Gregory N., et al.	257	52	07/19/2001
	US-6,521,958	02/18/2003	Forbes, L. , et al.	257	391	08/26/1999
	US-6,534,420	03/18/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-6,545,314	04/08/2003	Forbes, Leonard , et al.			05/15/2001
	US-6,552,387	04/22/2003	Eitan, Boaz	257	324	12/14/1998
	US-6,559,014	05/06/2003	Jeon, J.	438	287	10/15/2001
	US-6,567,303	05/20/2003	Hamilton, D. G., et al.	365	185.03	01/16/2002
	US-6,567,312	05/20/2003	Torii, Satoshi , et al.	365	185.28	10/13/2000
	US-6,570,787	05/27/2003	Wang, Z. , et al.	365	185.17	04/19/2002
	US-6,580,124	06/17/2003	Cleevies, James M., et al.	257	331	08/14/2000
	US-6,586,785	07/01/2003	Flagan, Richard C., et al.	257	261	06/29/2001

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, Journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
		ABBAS, S. A., et al., "N-Channel Igfet Design Limitations Due to Hot Electron Trapping", <u>Technical Digest, International Electron Devices Meeting..</u> Washington, DC,(December 1975),35-38		
		ADELmann, C , et al., "Atomic-layer epitaxy of GaN quantum wells and quantum dots on (0001) AlN", <u>Journal of Applied Physics, 91(8),</u> (April 15, 2002),5498-5500		
		AHN, SEONG-DEOK , et al., "Surface Morphology Improvement of Metalorganic Chemical Vapor Deposition Al Films by Layered Deposition of Al and Ultrathin TiN", <u>Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers), 39(6A),</u> (June 2000),3349-3354		

EXAMINER

DATE CONSIDERED

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 5 of 8		Attorney Docket No: 1303.058US2	

		AKASAKI, I. , "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N [0< x (< or =) 0.4] Films Grown on Sapphire Substrate by MOVPE", <u>Journal of Crystal Growth</u> , 98, (1989),209-219	
		ALEN, PETRA , et al., "Atomic Layer Deposition of Ta(Al)N(C) Thin Films Using Trimethylaluminum as a Reducing Agent", <u>Journal of the Electrochemical Society</u> , 148(10), (October 2001),G566-G571	
		ASARI, K , et al., "Multi-mode and multi-level technologies for FeRAM embedded reconfigurable hardware", <u>Solid-State Circuits Conference, 1999. Digest of Technical Papers. ISSCC. 1999 IEEE International</u> , 15-17 Feb. 1999, (1999),106 -107	
		BENJAMIN, M. , "UV Photoemission Study of Heteroepitaxial AlGaN Films Grown on 6H-SiC", <u>Applied Surface Science</u> , 104/105, (September 1996),455-460	
		BERMUDEZ, V. , "The Growth and Properties of Al and AlN Films on GaN(0001)-(1 x 1)", <u>Journal of Applied Physics</u> , 79(1), (January 1996),110-119	
		BRITTON, J , et al., "Metal-nitride-oxide IC memory retains data for meter reader", <u>Electronics</u> , 45(22), (October 23, 1972),119-23	
		CHAE, JUNGHUN , et al., "Atomic Layer Deposition of Nickel by the Reduction of Preformed Nickel Oxide", <u>Electrochemical & Solid-State Letters</u> , 5(6), (June 2002),C64-C66	
		CHAITSAK, SUTICAI , et al., "Cu(InGa)Se/sub 2/ thin-film solar cells with high resistivity ZnO buffer layers deposited by atomic layer deposition", <u>Japanese Journal of Applied Physics Part 1-Regular Papers Short Notes & Review Papers</u> , 38(9A), (September 1999),4989-4992	
		CRICCHI, J R., et al., "Hardened MNOS/SOS electrically reprogrammable nonvolatile memory", <u>IEEE Transactions on Nuclear Science</u> , 24(6), (December 1977),2185-9	
		DIMARIA, D J., "Graded or stepped energy band-gap-insulator MIS structures (GI-MIS or SI-MIS)", <u>Journal of Applied Physics</u> , 50(9), (September 1979),5826-5829	
		DIPERT, BRIAN , "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30(10), (October 1993),48-52	
		EITAN, BOAZ , "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell", <u>IEEE Electron Device Letters</u> , 21(11), (November 2000),543-545	
		ELAM, J W., "Kinetics of the WF6 and Si2H6 surface reactions during tungsten atomic layer deposition", <u>Surface Science</u> , 479(1-3), (May 2001),121-135	
		FERRIS-PRABHU, A V., "Amnesia in layered insulator FET memory devices", <u>Institution of Electrical Engineers</u> , (2002),Abstract	
		FERRIS-PRABHU, A V., "Charge transfer in layered insulators", <u>Institution of Electrical Engineers</u> , (2002),Abstract	
		FERRIS-PRABHU, A V., "Tunnelling theories of non-volatile semiconductor memories", <u>Physica Status Solidi A</u> , 35(1), (May 16, 1976),243-50	

EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 6 of 8		Attorney Docket No: 1303.058US2	

		FISCH, D E., et al., "Analysis of thin film ferroelectric aging", <u>Proc. IEEE Int. Reliability Physics Symp.</u> , (1990),237-242	
		FORBES, L. , et al., "Field Induced Re-Emission of Electrons Trapped in SiO", <u>IEEE Transactions on Electron Devices</u> , ED-26 (11), Briefs,(November 1979),1816-1818	
		FORSGREN, KATARINA , "Atomic Layer Deposition of HfO ₂ using hafnium iodide", Conference held in Monterey, California, (May 2001),1 page	
		FROHMAN-BENTCHKOWSKY, D , "An integrated metal-nitride-oxide-silicon (MNOS) memory", <u>Proceedings of the IEEE</u> , 57(6), (June 1969),1190-1192	
		GOODWINS, RUPERT , "New Memory Technologies on the Way", http://zdnet.com.com/2100-1103-846950.html , (February 2002),	
		GUHA, S , et al., "Atomic beam deposition of lanthanum-and yttrium-based oxide thin films for gate dielectrics", <u>Appl. Phys. Lett.</u> , 77, (2000),2710-2712	
		HWANG, C G., "Semiconductor Memories for the IT Era", <u>2002 IEEE International Solid-State Circuits Conference. Digest of Technical Papers IEEE</u> , Part vol. 1, San Francisco,(2002),24-27	
		HWANG, N. , et al., "Tunneling and Thermal Emission of Electrons from a Distribution of Deep Traps in SiO", <u>IEEE Transactions on Electron Devices</u> , 40(6), (June 1993),1100-1103	
		JUPPO, MARIKA , et al., "Use of 1,1Dimethylhydrazine in the Atomic Layer Deposition of Transition Metal Nitride Thin Films", <u>Journal of the Electrochemical Society</u> , 147(9), (September 2000),3377-3381	
		KLAUS, J W., et al., "Atomic layer deposition of tungsten nitride films using sequential surface reactions", <u>Journal of the Electrochemical Society</u> , 147(3), (March 2000),1175-81	
		KOO, J , "Study on the characteristics of TiAlN thin film deposited by atomic layer deposition method", <u>Journal of Vacuum Science & Technology A-Vacuum Surfaces & Films</u> , 19(6), (November 2001),2831-4	
		LEI, T. , "Epitaxial Growth and Characterization of Zinc-Blende Gallium Nitride on (001) Silicon", <u>Journal of Applied Physics</u> , 71(10), (May 1992),4933-4943	
		LUAN, H. , "High Quality Ta ₂ O ₅ Gate Dielectrics with Tox,eq<10A", <u>IEDM</u> , (1999),pp. 141-144	
		LUSKY, et al., "Characterization of channel hot electron injection by the subthreshold slope of NROM/sup TM/ device", <u>IEEE Electron Device Letters</u> , vol.22, no.11, (November 2001),556-558	
		MAAYAN, EDUARDO , et al., "A 512Mb NROM Flash Data Storage Memory with 8MB/s Data Rate", <u>Solid-State Circuits Conference, 2002. Digest of Technical Papers. ISSCC</u> , (2002),100-101	
		MARLID, BJORN , et al., "Atomic layer deposition of BN thin films", <u>Thin Solid Films</u> , 402(1-2), (January 2002),167-171	
		MIN, JAE-SIK , et al., "Atomic layer deposition of TiN films by alternate supply of tetrakis (ethylmethylamino)-titanium and ammonia", <u>Japanese Journal of Applied Physics Part 1-Regular Papers Short Notes & Review Papers</u> , vol.37, no.9A, (September 1998),4999-5004	

EXAMINER

DATE CONSIDERED

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 7 of 8		Attorney Docket No: 1303.058US2	

		MIN, J. , "Metal-organic atomic-layer deposition of titanium-silicon-nitride films", <u>Applied Physics Letters</u> , 75(11), (1999),1521-1523	
		MOAZZAMI, R , "Endurance properties of Ferroelectric PZT thin films", <u>Int. Electron Devices Mtg.</u> , San Francisco,(1990),417-20	
		MOAZZAMI, R , "Ferroelectric PZT thin films for semiconductor memory", <u>Ph.D Thesis</u> , University of California, Berkeley, (1991),	
		MOLNAR, R. , "Growth of Gallium Nitride by Electron-Cyclotron Resonance Plasma-Assisted Molecular-Beam Epitaxy: The Role of Charged Species", <u>Journal of Applied Physics</u> , 76(8), (October 1994),4587-4595	
		MORIWAKI, M , "Improved metal gate process by simultaneous gate-oxide nitridation during W/WN/sub x/gate formation", <u>Japanese Journal of Applied Physics Part 1-Regular Papers Short Notes & Review Papers</u> , 39(4B), (April 2000),2177-2180	
		NAKAJIMA, ANRI , "Soft breakdown free atomic-layer-deposited silicon-nitride/SiO ₂ /stack gate dielectrics", <u>International Electron Devices Meeting. Technical Digest</u> , (2001),6.5.1-4	
		PANKOVE, J. , "Photoemission from GaN", <u>Applied Physics Letters</u> , 25, (1974),53-55	
		PAPADAS, C. , "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", <u>IEEE Transaction on Electron Devices</u> , 42, (April 1995),678-682	
		PARK, JIN-SEONG , et al., "Plasma-Enhanced Atomic Layer Deposition of Tantalum Nitrides Using Hydrogen Radicals as a Reducing Agent", <u>Electrochemical & Solid-State Letters</u> , 4(4), (April 2001),C17-19	
		PUURUNEN, R L., et al., "Growth of aluminum nitride on porous silica by atomic layer chemical vapour deposition", <u>Applied Surface Science</u> , 165(2-3), (September 12, 2000),193-202	
		ROBERTSON, J. , "Band offsets of wide-band-gap oxides and implications for future electronic devices", <u>Journal of Vacuum Science & Technology B</u> (Microelectronics and Nanometer Structures), 18(3), (May-June 2000),1785-1791	
		SANDERS, B W., et al., "Zinc Oxysulfide Thin Films Grown by Atomic Layer Deposition", <u>Chemistry of Materials</u> , 4(5), (1992),1005-1011	
		SHE, MIN , et al., "Modeling and design study of nanocrystal memory devices", <u>IEEE Device Research Conference</u> , (2001),139-40	
		SHIMADA, H , et al., "Tantalum nitride metal gate FD-SOI CMOS FETs using low resistivity self-grown bcc-tantalum layer", <u>IEEE Transactions on Electron Devices</u> , vol.48, no.8, (August 2001),1619-1626	
		SHIROTA, R , et al., "A 2.3 mu m ² memory cell structure for 16 Mb NAND EEPROMs", <u>International Electron Devices Meeting 1990. Technical Digest</u> , San Francisco,(1990),103-106	
		SOLANKI, RAJ , et al., "Atomic Layer Deposition of Copper Seed Layers", <u>Electrochemical & Solid-State Letters</u> , 3(10), (October 2000),479-480	

EXAMINER

DATE CONSIDERED

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 8 of 8		Attorney Docket No: 1303.058US2	

		SZE, S M., "Physics of Semiconductor Devices", <u>New York : Wiley, (1981),504-506</u>	
		WEI, L S., et al., "Trapping, emission and generation in MNOS memory devices", <u>Solid-State Electronics, 17(6), (June 1974),591-8</u>	
		WHITE, M H., et al., "Characterization of thin-oxide MNOS memory transistors", <u>IEEE Transactions on Electron Devices, ED-19(12), (December 1972),1280-1288</u>	
		WHITE, M H., "Direct tunneling in metal-nitride-oxide-silicon (MNOS) structures", <u>Programmme of the 31st physical electronics conference, (1971),1</u>	
		WILK, G. D., et al., "High-K gate dielectrics: Current status and materials properties considerations", <u>Journal of Applied Physics, 89(10), (2001),5243-5275</u>	
		WOOD, S W., "Ferroelectric memory design", <u>M.A.Sc. thesis, University of Toronto, (1992),</u>	
		YAGISHITA, A , "Dynamic threshold voltage damascene metal gate MOSFET (DT-DMG-MOS) with low threshold voltage, high drive current and uniform electrical characteristics", <u>International Electron Devices Meeting 2000. Technical Digest. IEDM, (December 2000),663-666</u>	
		YODER, M , "Wide Bandgap Semiconductor Materials and Devices", <u>IEEE Transactions on Electron Devices, 43, (October 1996),1633-1636</u>	
		ZHU, W J., et al., "Current transport in metal/hafnium oxide/silicon structure", <u>IEEE Electron Device Letters, 23, (2002),97-99</u>	
		ZHU, W , et al., "HfO ₂ and HfAlO for CMOS: Thermal Stability and Current Transport", <u>IEEE International Electron Device Meeting 2001, (2001),463-466</u>	

EXAMINER

DATE CONSIDERED